

NPN SILICON RF TRANSISTOR **2SC5011**

NPN EPITAXIAL SILICON RF TRANSISTOR FOR HIGH-FREQUENCY LOW-NOISE AMPLIFICATION 4-PIN SUPER MINIMOLD

FEATURES

- High Gain Bandwidth Product (fr = 6.5 GHz TYP.)
- Low Noise, High Gain
- Low Voltage Operation
- 4-pin super minimold Package

★ ORDERING INFORMATION

Part Number	Quantity	Supplying Form	
2SC5011	50 pcs (Non reel)	• 8 mm wide embossed taping	
2SC5011-T1	3 kpcs/reel	• Pin 3 (Base), Pin 4 (Emitter) face to perforation side of the tape	

Remark To order evaluation samples, contact your nearby sales office. The unit sample quantity is 50 pcs.

ABSOLUTE MAXIMUM RATINGS (TA = +25°C)

Parameter	Symbol	Ratings	Unit
Collector to Base Voltage	Vсво	20	V
Collector to Emitter Voltage	VCEO	12	V
Emitter to Base Voltage	VEBO	3	V
Collector Current	lc	100	mA
Total Power Dissipation	Ptot Note	150	mW
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	-65 to +150	°C

Note Free air

Caution Observe precautions when handling because these devices are sensitive to electrostatic discharge.

The information in this document is subject to change without notice. Before using this document, please confirm that this is the latest version. Not all devices/types available in every country. Please check with local NEC Compound Semiconductor Devices representative for availability and additional information.

The mark \star shows major revised points.

ELECTRICAL CHARACTERISTICS (TA = +25°C)

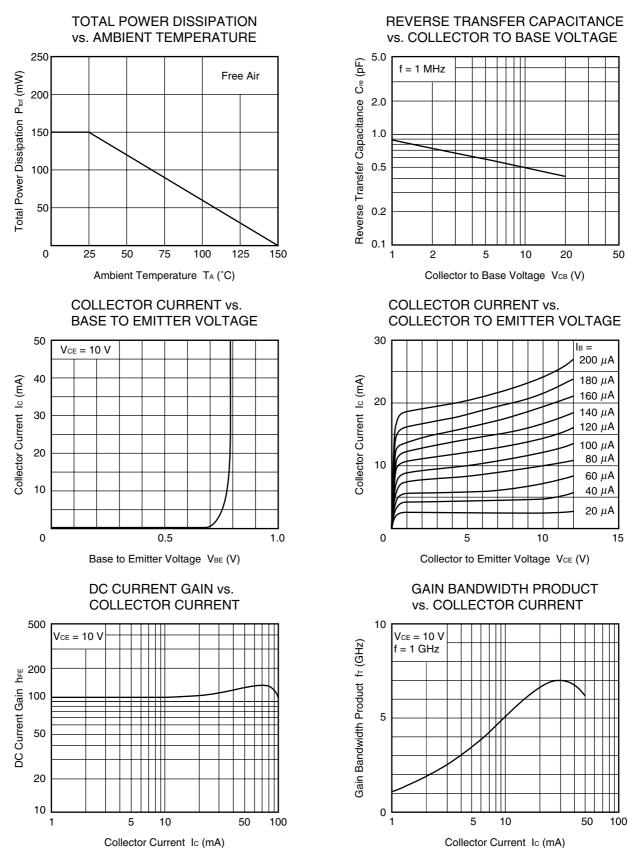
Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
DC Characteristics	-					
Collector Cut-off Current	Ісво	Vcb = 10 V, IE = 0 mA	-	-	1.0	μA
Emitter Cut-off Current	Іево	V _{EB} = 1 V, Ic = 0 mA	_	_	1.0	μA
DC Current Gain	hfe ^{Note 1}	Vce = 10 V, Ic = 20 mA	50	120	250	_
RF Characteristics						
Gain Bandwidth Product	f⊤	Vce = 10 V, Ic = 20 mA	_	6.5	-	GHz
Insertion Power Gain	S _{21e} ²	Vce = 10 V, Ic = 20 mA, f = 1.0 GHz	11	13	-	dB
Noise Figure	NF	Vce = 10 V, Ic = 7 mA, f = 1.0 GHz	-	1.1	2.0	dB
Reverse Transfer Capacitance	Cre ^{Note 2}	Vсв = 10 V, IE = 0 mA, f = 1.0 MHz	-	0.5	0.9	pF

Notes 1. Pulse measurement: PW \leq 350 μ s, Duty Cycle \leq 2%

2. Collector to base capacitance when the emitter grounded

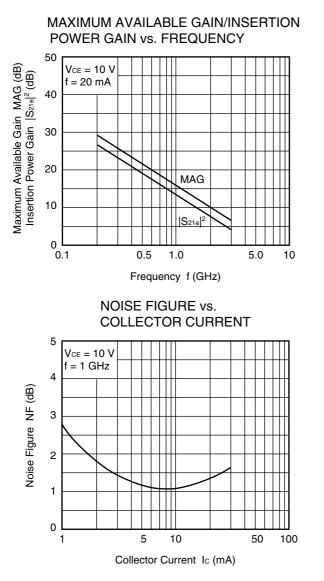
hfe CLASSIFICATION

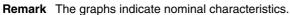
Rank	EB	FB	GB
Marking	R26	R27	R28
hfe Value	50 to 100	80 to 160	125 to 250



TYPICAL CHARACTERISTICS (TA = +25°C, unless otherwise specified)

Remark The graphs indicate nominal characteristics.





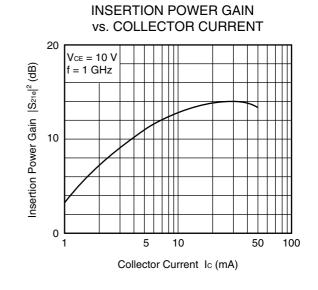
★ S-PARAMETERS

S-parameters/Noise parameters are provided on the NEC Compound Semiconductor Devices Web site in a form (S2P) that enables direct import to a microwave circuit simulator without keyboard input.

Click here to download S-parameters.

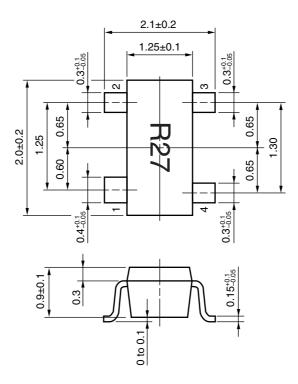
 $[\text{RF and Microwave}] \rightarrow [\text{Device Parameters}]$

URL http://www.ncsd.necel.com/



★ PACKAGE DIMENSIONS

4-PIN SUPER MINIMOLD (UNIT: mm)



PIN CONNECTIONS

- 1. Collector
- 2. Emitter
- 3. Base
- 4. Emitter

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▶ For further information, please contact

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